SiGe Semiconductor secures funding

SiGe Semiconductor, a supplier of analog integrated circuits for wireless access, cable telephony and high-speed optical systems, today announced it has raised US $42.8 million in Series B funding. The investment is the third highest round of financing closed by a fabless semiconductor company during the last year, according to the Fabless Semiconductor Association. The funds will support new product developments, as well as operations through to a cash flow positive position.

The lead investor was Boston-based TD Capital Technology Ventures, joined by new United States investors 3i US and Prism Venture Partners, along with returning investors VenGrowth Capital Partners Inc., CDP Capital - Technology Ventures, Business Development Bank of Canada (BDC), Capital Alliance Ventures, and Canadian Science & Technology Growth Fund.

"We are proud of our continued successes in light of current market conditions," said Jim Derbyshire, president and CEO, SiGe Semiconductor. "We've followed the right strategy in diversifying our product lines into markets where our core technology - silicon germanium - provides significant advantages. This has both protected our company from the downturn, and fueled our growth, giving investors an overwhelming confidence in our ability to achieve our vision."

SiGe Semiconductor's integrated circuits are designed using silicon germanium technology that improves performance, battery life and size of a wide range of wireless and broadband products, including: Bluetooth™-enabled portable devices, WLAN access points, high-speed optical interfaces, global positioning by satellite systems, cordless telephones, and 2G, 2.5G and 3G cellular handsets.

"SiGe Semiconductor is a very exciting company with a clear vision, and the business acumen to achieve it," said Paul Ciriello, managing director, TD Capital Technology Ventures. "TD Capital made this investment because of SiGe's valuable and sustainable technology assets, and its strong and experienced management team."

New members of SiGe's board of directors with this round of funding include Paul Ciriello, TD Capital Technology Ventures; Mikko Suonenlahti, 3i US; and Robert Fleming, Prism Venture Partners. They will join existing members Patrick DiPietro, VenGrowth Capital Partners Inc.; Denis Colbourne, former head of Nortel Semiconductor; Doug Smeaton, Semiconductor Insights and Jim Derbyshire, SiGe Semiconductor. John Millard, former CEO of Mitel Corporation, and René Séguin, BDC will retire from SiGe's board.

The funding reflects SiGe Semiconductor's success during the last two years, during which the company increased product revenues, extended support and distribution channels, brought their sixteenth product to market, and established new facilities in Hong Kong, San Diego, Boston, and London, UK. SiGe Semiconductor has delivered over five million integrated circuits to a world-class customer base that includes Alps, Arris, Bromax, Gemtek, LG Innotek, Micro-Star, Microtune, Photon, Samsung Electro-Mechanics, and Stratos Lightwave.

Motorola wins manufacturing technology award

The Board of Directors of the International Conference on Compound Semiconductor Manufacturing Technology at its meeting in New Orleans on Dec. 6th, 2002, announced the winners of the awards for the best papers presented at the 2002 meeting last April.

The choice of winners is made by the Board based on feedback from conference attendees and input from the conference Technical Program Committee. These papers were selected from a total of nearly seventy papers presented.

Winning the He Bong Kim Award for best conference paper were Mariam Sadaka, Darrell Hill, Fred Clayton, Haldane Henry, Colby Rampley, Jon Abrokwah, and Ric Uscola of Motorola Semiconductor Products, Tempe, Arizona, for a paper entitled "Development of Motorola's InGaP HBT Process." This paper described the development of a high volume, robust process for fabrication of high performance C-doped InGaP/GaAs HBTs on 150mm wafers.

The Best Student Paper Award winners were M. L. Hattendorf, Q. J. Hartmann, K. Richards, and M. Feng of the University of Illinois, for a paper entitled "Submicron Scaling of High-Speed InP/InGaAs SHBTs Grown by MOCVD using Carbon as the p-type Dopant." This paper described the demonstration of the effectiveness of lateral scaling as a technique for obtaining excellent rf performance for standard double-mesa HBTs.

This is a significant achievement for the authors and their organizations. Awards will be presented at the 18th meeting of this conference scheduled to be held May 19th-23rd, 2003, at the Camelback Inn in Scottsdale, AZ (for further information, visit the web site at www.gaasmantech.org).

Quantum dot external cavity laser on show

Aculight Corporation and Zia Laser, Inc. are planning a collaborative demonstration of a broadly-tunable Quantum Dot (QD) External Cavity Laser (ECL) at Photonics West.
The ECL is based upon Zia's QD Gallium Arsenide 1300-nm gain chip combined with Aculight's external cavity design. Zia's featured "DWELL(TM)," Dots-In-A-Well, technology enables broad tunability through engineered Quantum Dot nanostructures grown within the active region of the laser. The displayed QD ECL is capable of tuning over a 100-nm range with a maximum output power of 3 mW cw. Aculight's and Zia's combined technologies enable spectroscopic measurements over broader tuning ranges than are possible with more conventional quantum well devices. Extensions to the displayed laser include access to several wavelength regions, rapid tuning capability, coupling to single-mode or multi-mode fibers, and generation of a broadband output. Applications include medical diagnostics (spectroscopic and imaging modalities), test and measurement, and spectroscopy.